

D5SB60

PRV : 600 Volts

Io : 6 Amperes

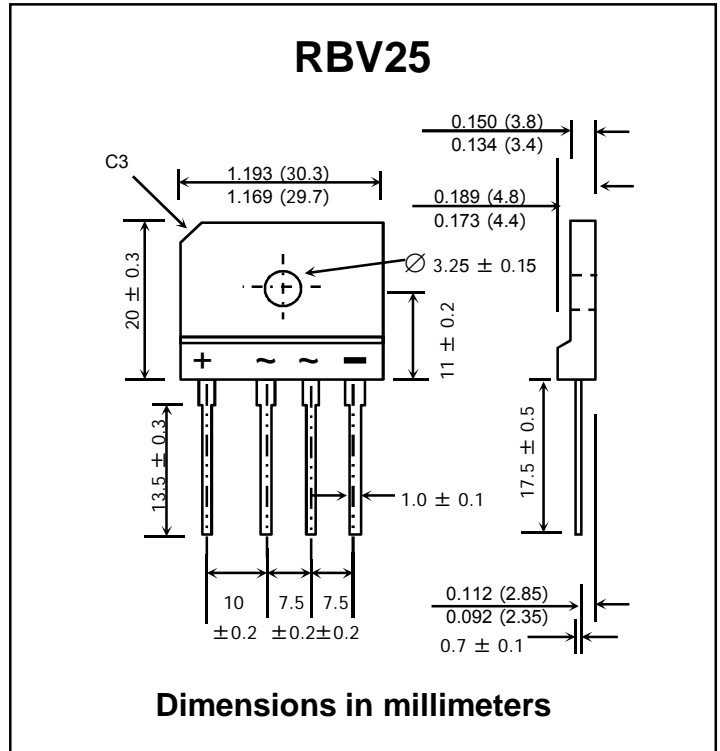
FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Ideal for printed circuit board
- * Very good heat dissipation
- * **Pb / RoHS Free**

MECHANICAL DATA :

- * Case : Reliable low cost construction utilizing molded plastic technique
- * Epoxy : UL94V-0 rate flame retardant
- * Terminals : Plated lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Polarity symbols marked on case
- * Mounting position : Any
- * Weight : 7.7 grams

SILICON BRIDGE RECTIFIERS



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.

RATING	SYMBOL	VALUE	UNIT
Maximum Reverse Voltage	VRM	600	V
Maximum Average Forward Current (50Hz Sine wave, R-load)	IF(AV)	6 (With heatsink, Tc = 110°C) 2.8 (Without heatsink, Ta = 25°C)	A
Maximum Peak Forward Surge Current, Tj = 25°C (50Hz sine wave, Non-repetitive 1 cycle peak value)	IFSM	170	A
Current Squared Time at 2ms ≤ t < 10 ms, Tc=25°C	I ² t	140	A ² S
Maximum Forward Voltage per Diode at IF = 3.0 A	VF	1.05	V
Maximum DC Reverse Current, VR=VRM (Pulse measurement, Rating of per diode)	IR	10	μA
Maximum Thermal Resistance, Junction to case	RθJC	3.4 (With heatsink)	°C/W
Maximum Thermal Resistance, Junction to Ambient	RθJA	26 (Without heatsink)	°C/W
Operating Junction Temperature	TJ	150	°C
Storage Temperature Range	TSTG	- 40 to + 150	°C

RATING AND CHARACTERISTIC CURVES (D5SB60)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

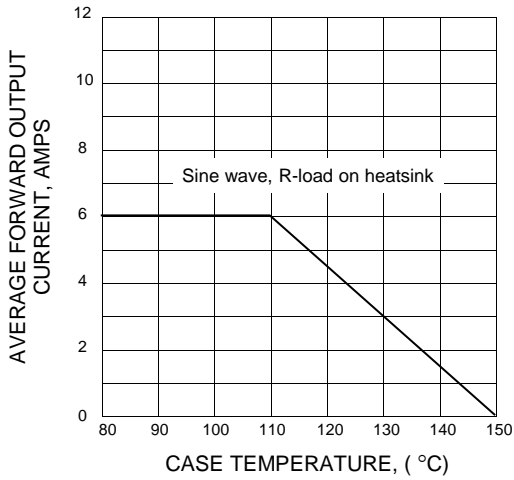


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

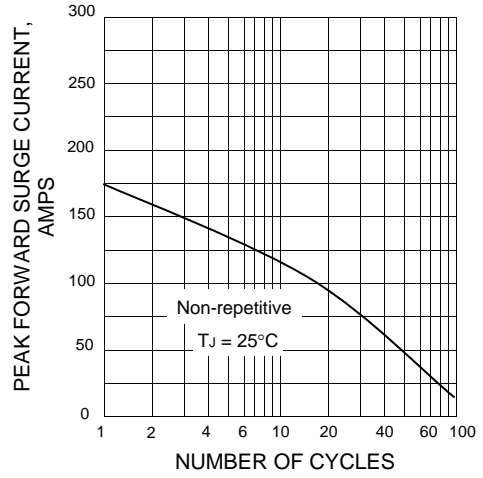


FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE

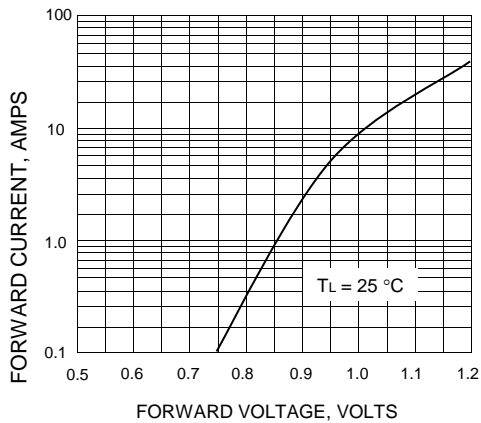


FIG.4 - POWER DISSIPATION

